MOSFETs Silicon N-Channel MOS (DTMOSIV)

TK49N65W

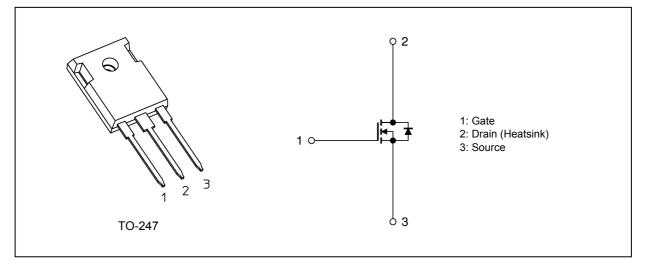
1. Applications

Switching Voltage Regulators

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 0.048 \Omega$ (typ.) by using Super Junction Structure : DTMOS
- (2) Easy to control Gate switching
- (3) Enhancement mode: V_{th} = 2.5 to 3.5 V ($V_{\rm DS}$ = 10 V, $I_{\rm D}$ = 2.5 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

Characteristics			Rating	Unit
Drain-source voltage		V _{DSS}	650	V
Gate-source voltage		V _{GSS}	±30	1
Drain current (DC)	(Note 1)	I _D	49.2	A
Drain current (pulsed)	(Note 1)	I _{DP}	196	1
Power dissipation (T _c =	25°C)	PD	400	W
Single-pulse avalanche energy	(Note 2)	E _{AS}	764	mJ
Avalanche current		I _{AR}	13	A
Reverse drain current (DC)	(Note 1)	I _{DR}	49.2	1
Reverse drain current (pulsed)	(Note 1)	I _{DRP}	196	7
Channel temperature		T _{ch}	150	°C
Storage temperature		T _{stg}	-55 to 150	7
Mounting torque		TOR	0.8	N · m

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production

5. Thermal Characteristics

Characteristics		Max	Unit
Channel-to-case thermal resistance	R _{th(ch-c)}	0.313	°C/W
Channel-to-ambient thermal resistance	R _{th(ch-a)}	50	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: V_DD = 90 V, T_ch = 25°C (initial), L = 8 mH, R_G = 25 Ω , I_AR = 13 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics (Ta = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I _{GSS}	V_{GS} = ±30 V, V_{DS} = 0 V	_	_	±1	μA
Drain cut-off current	I _{DSS}	V _{DS} = 650 V, V _{GS} = 0 V	_	_	10	
Drain-source breakdown voltage	V _{(BR)DSS}	I _D = 10 mA, V _{GS} = 0 V	650	—	—	V
Gate threshold voltage	V _{th}	V _{DS} = 10 V, I _D = 2.5 mA	2.5	_	3.5	
Drain-source on-resistance	R _{DS(ON)}	V _{GS} = 10 V, I _D = 24.6 A		0.048	0.055	Ω

6.2. Dynamic Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C _{iss}	V _{DS} = 300 V, V _{GS} = 0 V, f = 100 kHz	_	6500	_	pF
Reverse transfer capacitance	C _{rss}]	_	15	_	
Output capacitance	C _{oss}	1	_	140	_	
Effective output capacitance	C _{o(er)}	V_{DS} = 0 to 400 V, V_{GS} = 0 V	_	200	_	
Gate resistance	r _g	V _{DS} = OPEN, f = 1 MHz	_	2	_	Ω
Switching time (rise time)	tr	See Figure 6.2.1	_	70		ns
Switching time (turn-on time)	t _{on}	1	_	130	_	
Switching time (fall time)	t _f		_	10	_	
Switching time (turn-off time)	t _{off}]	_	270		
MOSFET dv/dt ruggedness	dv/dt	V _{DD} = 0 to 400 V, I _D = 24.6 A	50	_	_	V/ns

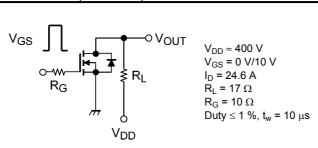


Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx 400 \text{ V}, \text{ V}_{GS}$ = 10 V, I _D = 49.2 A	_	160	_	nC
Gate-source charge 1	Q _{gs1}		_	40	_	
Gate-drain charge	Q _{gd}		_	60	_	

6.4. Source-Drain Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	V _{DSF}	I _{DR} = 49.2 A, V _{GS} = 0 V	_		-1.7	V
Reverse recovery time	t _{rr}	I _{DR} = 24.6 A, V _{GS} = 0 V	_	500	_	ns
Reverse recovery charge	Q _{rr}	-dI _{DR} /dt = 50 A/μs	_	7	_	μC
Peak reverse recovery current	I _{rr}		_	25	_	А
Diode dv/dt ruggedness	dv/dt	I_{DR} = 24.6 A, V_{GS} = 0 V, V_{DD} = 400 V	15			V/ns

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7. Marking (Note)

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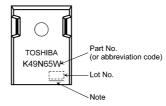
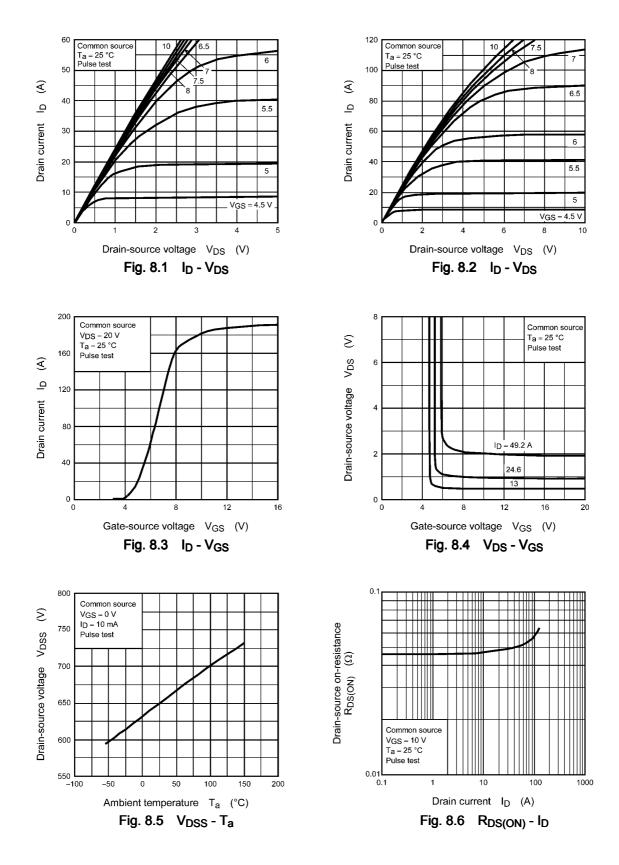
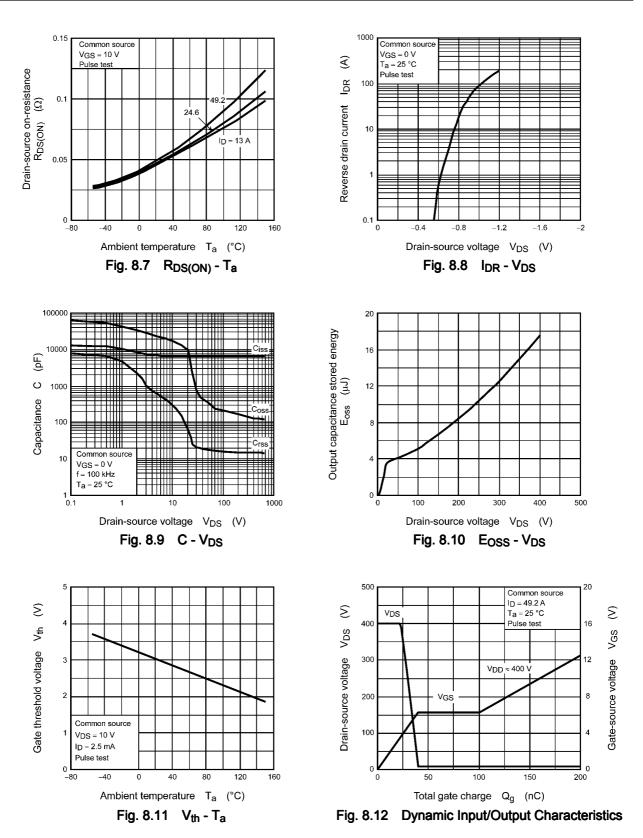


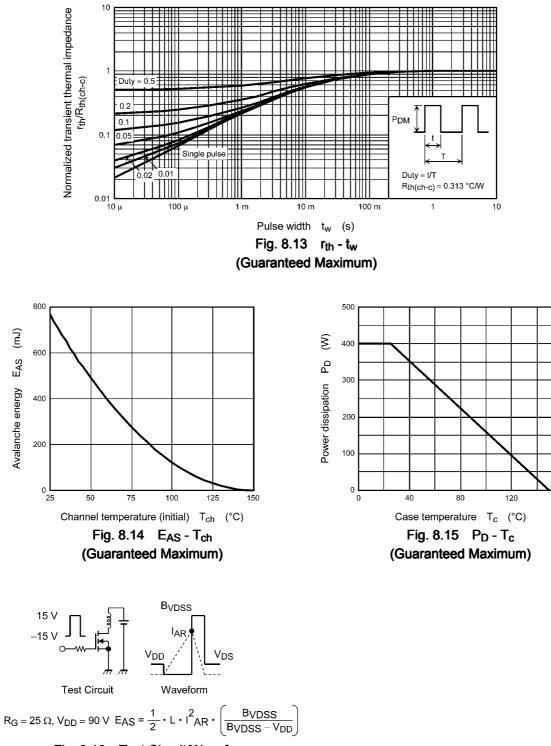
Fig. 7.1 Marking

 Note: A line under a Lot No. identifies the indication of product Labels. Not underlined: [[Pb]]/INCLUDES > MCV Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]] Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product. The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

8. Characteristics Curves (Note)

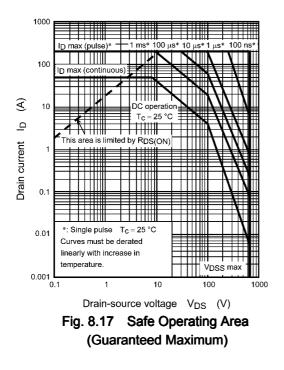








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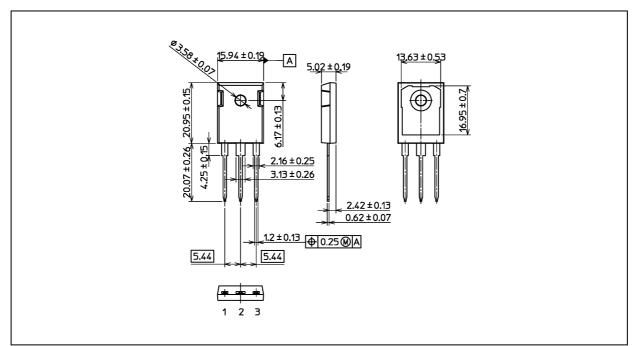


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 6.15 g (typ.)

F	Package Name(s)
JEITA: SC-65	
TOSHIBA: 2-16L1A	
Nickname: TO-247	

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